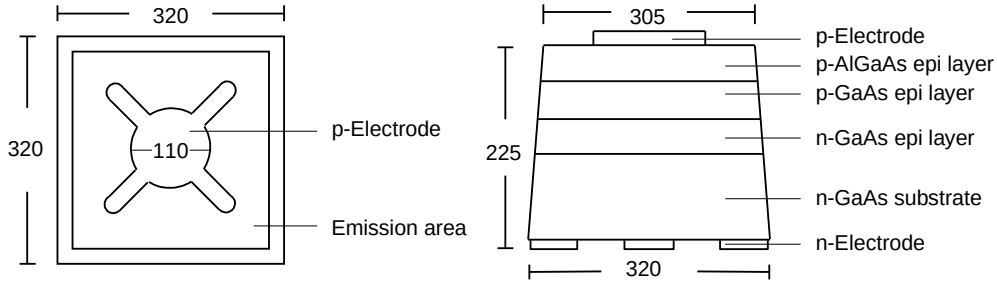
Features :

- AlGaAs/GaAs Wafer
- Good Spectral Matched to Si Detector
- High Power
- Low Forward Voltage

Typical Applications :

- Remote Controller
- Peripherals
- Photo Coupler
- Photo Interrupter

Outline Dimensions : (Unit: um)



Physical Structure :

Chip dimension	Chip size	320 um x 320 um
	Thickness	225 um
	Emission area	305 um
	Bonding pad	110 um
Electrode	Top: P (anode)	Gold
	Backside: N (cathode)	Gold alloy
Surface condition	Frosted	

Electro-Optical Characteristics : (Ta = 25℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	I_F = 100 mA	-	1.34	1.60	V
		I_F = 200 mA	-	1.47	1.80	
Reverse Voltage	V_R	I_R = 10 uA	5	-	-	V
Wavelength	λ_p	I_F = 20 mA	-	940	-	nm
Spectral width at half height	$\triangle\lambda$	I_F = 20 mA	-	50	-	nm
Radiant Power	P_o	I_F = 20 mA	0.90	-	-	mW

※ ED-014IRA-T is not suitable for package of electrical white board application without adding soft gel. OPTOTECH suggests applying ED-E14IRA for electrical white board application.

Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. DC Forward Voltage

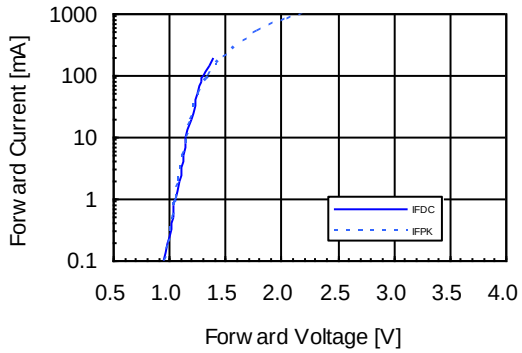


Fig 2. Relative Radian Power vs. Wavelength

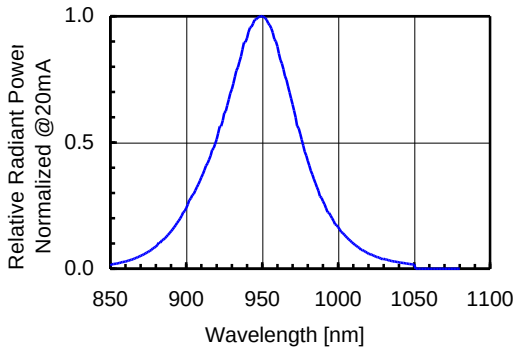


Fig 3. Relative Radiant Power vs. Forward DC Current

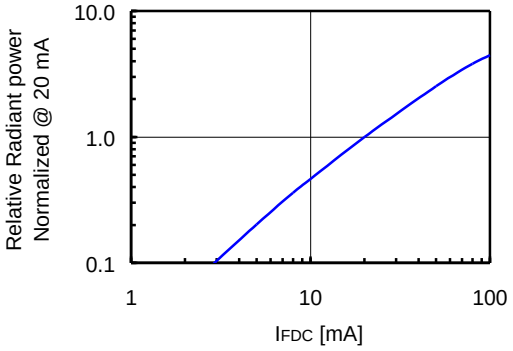


Fig 4. Relative Radiant Power Vs. Forward Peak Current

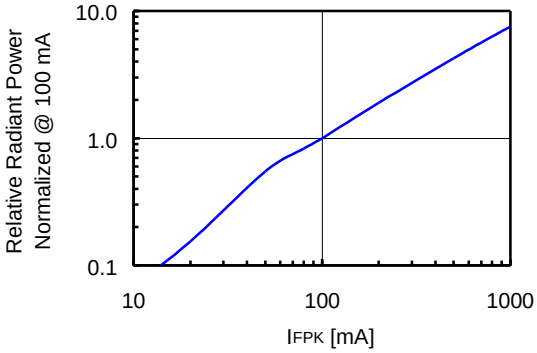


Fig 5. Forward DC Voltage vs. Temperature

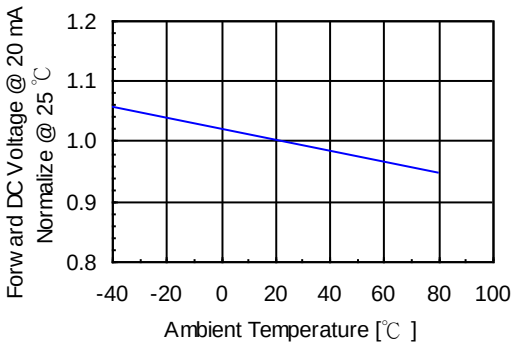


Fig 6. Relative Radiant Power vs. Temperature